

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently amended) A ferroelectric capacitor, comprising:
 - a first electrode layer located over a substrate, wherein the first electrode layer includes iridium;
 - an oxide electrode template located over the first electrode layer;
 - a ferroelectric dielectric layer located over the oxide electrode template, wherein the oxide electrode template and the ferroelectric dielectric layer have substantially similar crystal structures; and
 - a second electrode layer located over the ferroelectric dielectric layer.
2. (Original) The ferroelectric capacitor as recited in claim 1 wherein the oxide electrode template forms a portion of a first electrode.
3. (Original) The ferroelectric capacitor as recited in Claim 1 wherein the oxide electrode template comprises a perovskite material.
4. (Original) The ferroelectric capacitor as recited in Claim 1 wherein the oxide electrode template comprises a distorted perovskite material.
5. (Original) The ferroelectric capacitor as recited in Claim 1 wherein the oxide electrode template is selected from the group consisting of SrIrO₃ and SrRuO₃.

6. (Original) The ferroelectric capacitor as recited in Claim 1 wherein the oxide electrode template is selected from the group consisting of BaPbO₃, PbIrO₃, PbRuO₃, BiRuO₃, BilrO₃, (La,Sr)CoO₃, CaRuO₃, and BaPbO₃.

7. (Original) The ferroelectric capacitor as recited in Claim 1 wherein the oxide electrode template has a thickness ranging from about 20 nm to about 100 nm.

8. (Original) The ferroelectric capacitor as recited in Claim 1 wherein the oxide electrode template has a resistivity less than about 400 micro-ohms/cm.

9. (Cancelled)

10. (Original) The ferroelectric capacitor as recited in Claim 1 wherein the oxide electrode template is a first oxide electrode template and further including a second oxide electrode template located between the ferroelectric dielectric layer and the second electrode layer.

Claims 11-20. (Cancelled)

21. (Currently amended) A ferroelectric random access memory (FeRAM) device, comprising:

a transistor having source/drain regions located over a semiconductor substrate;

an interlevel dielectric layer located over the transistor, the interlevel dielectric layer having a conductive plug therein contacting at least one of the source/drain regions; and

a ferroelectric capacitor located over the interlevel dielectric layer and contacting the conductive plug, including;

 a first electrode layer located over the interlevel dielectric layer, wherein the first electrode layer includes iridium;

 an oxide electrode template located over the first electrode layer;

 a ferroelectric dielectric layer located over the oxide electrode template,
wherein the oxide electrode template and the ferroelectric dielectric layer have substantially similar crystal structures; and

 a second electrode layer located over the ferroelectric dielectric layer.

22. (Original) The ferroelectric random access memory (FeRAM) device as recited in Claim 21 wherein at least a portion of the transistor includes a nickel silicide.